TOSHIBA Intelligent Power Device Silicon Monolithic Power MOS Integrated Circuit

TPD1034F

High-side Power Switch for Motors, Solenoids, and Lamp Drivers

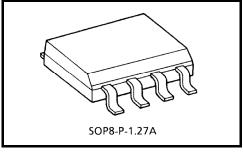
The TPD1034F is a monolithic power IC for high-side switches. The IC has a vertical MOS FET output which can be directly driven from a CMOS or TTL logic circuit (e.g., an MPU). The device offers intelligent self-protection and diagnostic functions.

Features

on a single chip.

- A monolithic power IC with a new structure combining a control block (Bi-CMOS) and a vertical power MOS FET (π-MOS)
- One side of the load can be grounded to a high-side switch.
- Can directly drive a power load from a microprocessor.
- Built-in protection against thermal shutdown and load short-circuiting.
- Incorporates a diagnosis function that allows diagnosis output to be read externally at load short-circuiting, opening, or overtemperature
- Up to −10 V of counter electromotive force from an L load can be applied.
- Low on-resistance : $RON = 80 \text{ m}\Omega \text{ (max)}$
- Low operating current : IDD = 1 mA (typ.), (@VDD = 12 V, VIN = 0 V)
- 8-pin SOP package for surface mounting can be packed in tape.

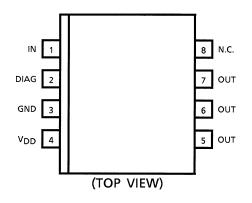
Note: Due to its MOS structure, this product is sensitive to static electricity. Handle with care.

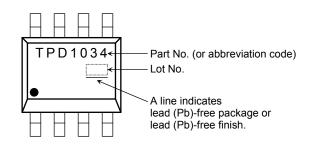


Weight: 0.08 g (typ.)

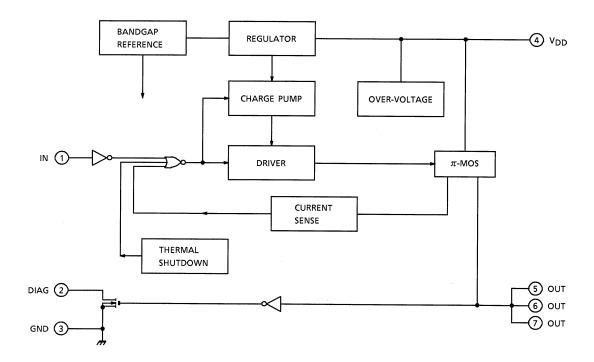
Pin Assignment

Marking





Block Diagram

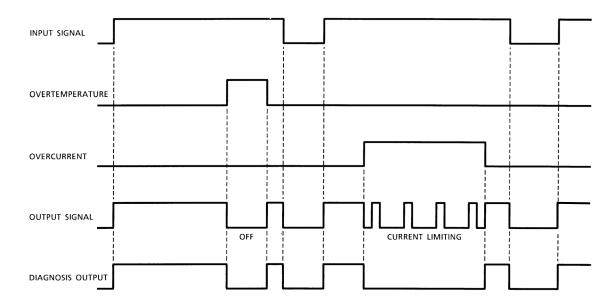


Pin Description

| Pin No. | Symbol | Function |
|---------|----------|--|
| 1 | IN | Input pin. Input is CMOS-compatible, with pull-down resistor connected. Even if the input is open, output will not accidentally turn on. |
| 2 | DIAG | Self-diagnosis detection pin. Goes low when overheating is detected or when output is short-circuited with input on (high). n-channel open drain. |
| 3 | GND | Ground pin. |
| 4 | V_{DD} | Power pin. |
| 5, 6, 7 | OUT | Output pin. When the load is short circuited and current in excess of the detection current (24A typ.) flows to the output pin, the output automatically turns on or off. |

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Timing Chart



Truth Table

| Input Signal | Output Signal | Diagnosis Output | State | |
|--------------|---------------|------------------|-----------------|--|
| Н | Н | Н | Normal | |
| L | L | L | Noma | |
| Н | L | L | Overcurrent | |
| L | L | L | Overcurrent | |
| Н | Н | Н | Load open | |
| L | Н | Н | Load open | |
| Н | L | L | Overtemperature | |
| L | L | L | Overtemperature | |

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Absolute Maximum Ratings (Ta = 25°C)

| Characteristic | | Symbol | Rating | Unite |
|-------------------------------|-------|---------------------|--|-------|
| Drain-source voltage | | V _{DS} | 60 | V |
| Supply voltage | DC | V _{DD (1)} | 25 | V |
| Supply voltage | Pulse | V _{DD (2)} | 60 (Rs = 1Ω, τ= 250 ms) | V |
| Input voltage | DC | V _{IN (1)} | − 0.5 ~ 12 | V |
| Input voltage | Pulse | V _{IN (2)} | V _{DD (1)} + 1.5 (t = 100 ms) | V |
| Diagnosis output voltage | | V _{DIAG} | − 0.5 ~ 25 | V |
| Output current | | Io | Internally limited | Α |
| Input current | | I _{IN} | ±10 | mA |
| Diagnosis output current | | I _{DIAG} | 5 | mA |
| Power dissipation (Ta = 25°C) | | D- | 1.4 (Note 1) | W |
| | | P _D | 2.4 (Note 2) | VV |
| Operating temperature | | T _{opr} | − 40 ~ 110 | °C |
| Channel temperature | | T _{ch} | 150 | °C |
| Storage temperature | | T _{stg} | − 55 ~ 150 | °C |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Resistance

| Characteristic | Symbol | Test Condition | Unit | |
|--------------------|------------------------|----------------|-------|--|
| Thermal resistance | R _{th (ch-a)} | 89.3 (Note 1) | °C/W | |
| Thema resistance | in (cn-a) | 52.1 (Note 2) | 0 / W | |

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Note1: Mounted on a glass epoxy board (25.4 mm \times 25.4 mm \times 0.8 mm) (DC) Note2: Mounted on a glass epoxy board (25.4 mm \times 25.4 mm \times 0.8 mm) ($t_W \le 10$ s)

Electrical Characteristics (Unless otherwise specified, T_{ch} = - 40 ~ 110°C, V_{DD} = 8 ~ 18 V)

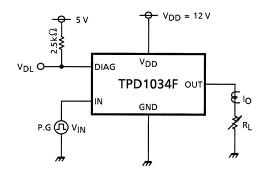
| Characteri | Symbol | Test Cir- cuit | Test Condition | Min | Тур. | Max | Unit | |
|--------------------------|------------------------|------------------------------|-----------------------|---|------|-----|------|----|
| Operating supply volta | V _{DD} (opr) | _ | _ | 5 | 12 | 18 | V | |
| Supply current | | I _{DD} | _ | V _{DD} = 12 V, V _{IN} = 0 | _ | 1 | 5 | mA |
| Innut voltage | | V _{IH} | _ | V _{DD} = 12 V, I _O = 8 A | 3.5 | _ | _ | V |
| input voltage | Input voltage | | _ | V _{DD} = 12 V, I _O = 1.2 mA | _ | _ | 1.5 | V |
| Input current | | I _{IN (1)} | _ | V _{DD} = 12 V, V _{IN} = 5 V | _ | 50 | 200 | μΑ |
| | | I _{IN (2)} | _ | V _{DD} = 12 V, V _{IN} = 0 | -0.2 | _ | 0.2 | μΑ |
| On-voltage | | V _{DS (ON)} | _ | V _{DD} = 12 V, I _O = 8 A, T _{ch} = 25°C | _ | _ | 0.64 | V |
| On-resistance | | R _{DS (ON)} | _ | V _{DD} = 12 V, I _O = 8 A, T _{ch} = 25°C | _ | _ | 0.08 | Ω |
| Output leakage current | Output leakage current | | _ | V _{DD} = 18 V, V _{IN} = 0 | _ | _ | 1.2 | mA |
| Diagnosis output voltage | "L" Level | V_{DL} | _ | V _{DD} =12 V, I _{DL} = 2 mA | _ | _ | 0.4 | V |
| Diagnosis output current | "H" Level | I _{DH} | _ | V _{DD} = 18 V, V _{DH} = 18 V | _ | _ | 10 | μΑ |
| Overcurrent protection | | I _{S (1)} Note 3 | 1 | V _{DD} = 12 V, T _{ch} = 25°C | 8 | 12 | _ | Α |
| | | I _{S (2)} Note 4 | 2 | VDD = 12 V, 1ch = 23 C | 15 | 24 | _ | Α |
| The man of a building | Temperature | Ts | _ | | 150 | 160 | 200 | °C |
| Thermal shutdown | Hysteresis | ΔTs | _ | _ | _ | 10 | _ | °C |
| Open detection resista | R _{ops} | _ | V _{DD} = 8 V | 1 | 50 | 100 | kΩ | |
| Switching time | | ton | 3 | $V_{DD} = 12 \text{ V}, R_L = 5\Omega,$ $T_{ch} = 25^{\circ}\text{C}$ | 10 | 200 | _ | μs |
| | | tOFF | 3 | | 10 | 30 | _ | μs |

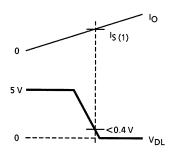
Note 3: $I_{S(1)}$ denotes the overcurrent detection value when the load is short circuited and V_{IN} = "L" \rightarrow "H"

Note 4: $I_{S(2)}$ denotes the overcurrent detection value when the load current is increased while V_{IN} = "H"

Test Circuit 1

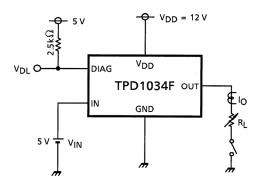
Overcurrent detection

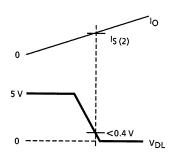




Test Circuit 2

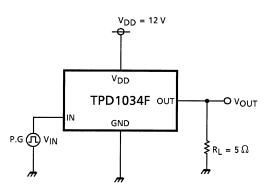
Overcurrent detection

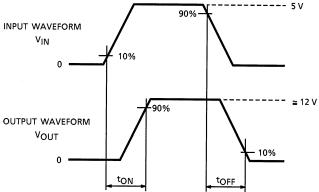


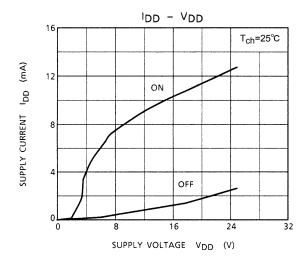


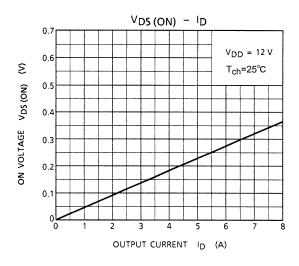
Test Circuit 3

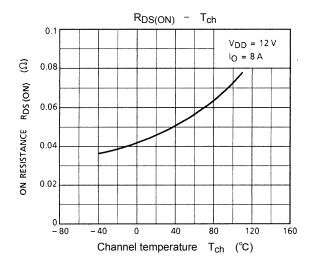
Switching time

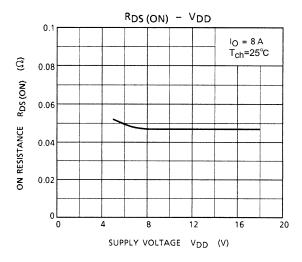


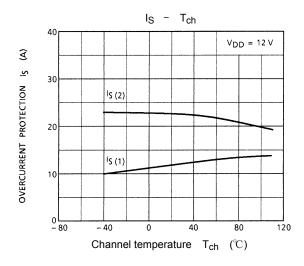


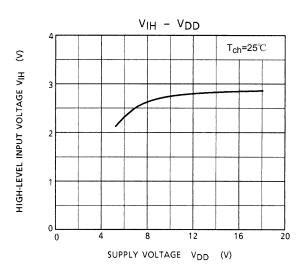


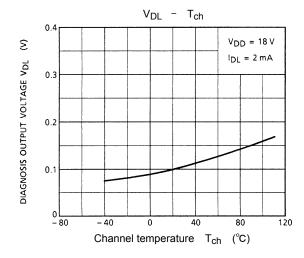


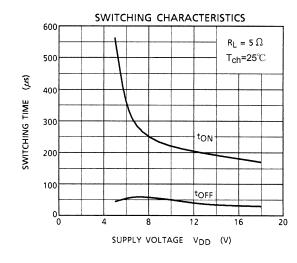


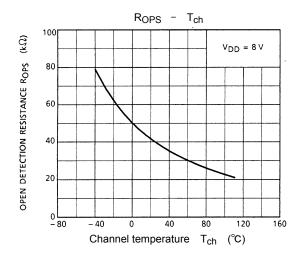


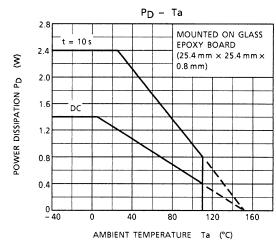


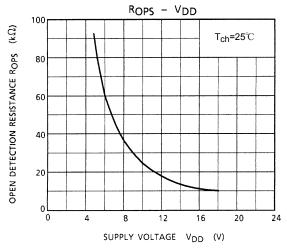








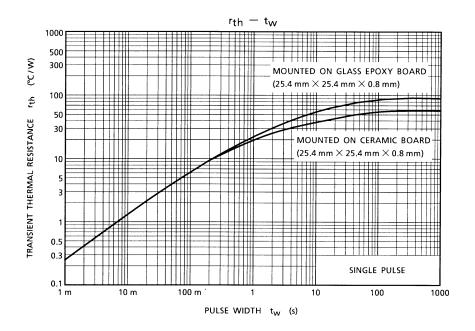




Precaution:

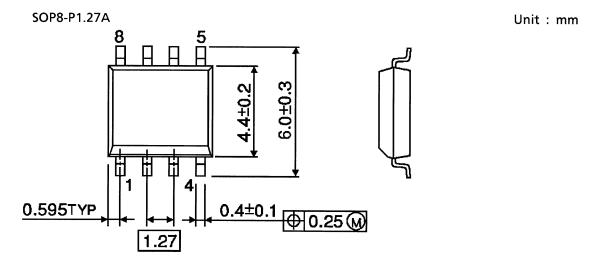
1. Since there is no built-in protection against reverse connection of batteries, etc., provide such protection using external circuits.

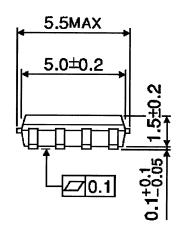
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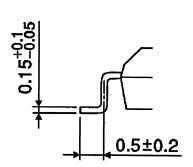


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Package Dimensions







Weight: 0.08 g (typ.)

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